
	<p>SI2333DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2333DS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 12V 4.1A SOT23-3</p> <p>Datenblätter:  SI2333DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 144375 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2333DS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 12V 4.1A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	144375 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.1A (Ta)
Rds On (Max) @ Id, Vgs	32 mOhm @ 5.3A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	18nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	1100pF @ 6V
Verpackung	Tape & Reel (TR)








SI2333DS-T1-GE3 ist neu im Original, Suche SI2333DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2333DS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2333DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2335DS-T1-E3 Vishay / Siliconix MOSFET P-CH 12V 3.2A SOT23</p>	 <p>SI2334DS-T1-E3 V SI2334DS-T1-E3 V</p>	 <p>SI2333DS 89K SI2333DS 89K</p>	 <p>SI2333DS-T1-E3 Vishay / Siliconix MOSFET P-CH 12V 4.1A SOT23-3</p>
 <p>SI2335DS-T1 VISHAY SI2335DS-T1 VISHAY</p>	 <p>SI2334DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 4.9A SOT-23</p>	 <p>SI2334DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 4.9A SOT-23</p>	 <p>SI2333DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 4.1A SOT23-3</p>

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|  SI2328DS-T1-E3 |  SI2328DS-T1-E3 |  SI2328DS-T1-GE3 |  SI2328DS-T1-GE3 |  SI2329DS-T1-E3 |
|  SI2329DS-T1-GE3 |  SI2329DS-T1-GE3 |  SI2331DS |  SI2331DS-T1-E3 |  SI2331DS-T1-E3 |
|  SI2331DS-T1-GE3 |  SI2331DS-T1-GE3 |  SI2333ADS-T1-GE3 |  SI2333CDS |  SI2333CDS-T1-E3 |
|  SI2333CDS-T1-E3 |  SI2333CDS-T1-GE3 |  SI2333CDS-T1-GE3 |  SI2333DDS-T1-E3 |  SI2333DDS-T1-GE3 |
|  SI2333DDS-T1-GE3 |  SI2333DS |  SI2333DS-T1-E3 |  SI2333DS-T1-E3 |  SI2333DS-T1-GE3 |
|  SI2334DS-T1-E3 |  SI2334DS-T1-GE3 |  SI2334DS-T1-GE3 |  SI2335DS-T1 |  SI2335DS-T1-E3 |
|  SI2335DS-T1-E3 |  SI2335DS-T1-GE3 |  SI2335DS-T1-GE3 |  SI2336DS-T1-E3 |  SI2336DS-T1-GE3 |
|  SI2336DS-T1-GE3 |  SI2337DS |  SI2337DS-T1-E3 |  SI2337DS-T1-E3 |  SI2337DS-T1-GE3 |
|  SI2337DS-T1-GE3 |  SI2338DS-T1-E3 |  SI2338DS-T1-GE3 |  SI2338DS-T1-GE3 |  SI2341DS |
|  SI2341DS-T1-E3 |  SI2341DS-T1-E3 |  SI2341DS-T1-GE3 |  SI2341DS-T1-GE3 |  SI2342DS-T1-E3 |

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